

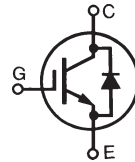
High Voltage, High Gain BIMOSFET™ Monolithic Bipolar MOS Transistor

IXBF20N300

$$V_{CES} = 3000V$$

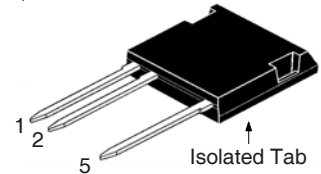
$$I_{C110} = 14A$$

$$V_{CE(sat)} \leq 3.2V$$



(Electrically Isolated Tab)

ISOPLUS i4-Pak™



1 = Gate
2 = Emitter

5 = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_C = 25^\circ C$ to $150^\circ C$	3000	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	3000	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$	34	A
I_{C110}	$T_C = 110^\circ C$	14	A
I_{CM}	$T_C = 25^\circ C$, 1ms	150	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 125^\circ C$, $R_G = 20\Omega$	$I_{CM} = 130$	A
	Clamped Inductive Load	1500	V
P_C	$T_C = 25^\circ C$	150	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
T_{SOLD}	Plastic Body for 10 seconds	260	$^\circ C$
F_C	Mounting Force	20..120 / 4.5..27	Nm/lb.in.
V_{ISOL}	50/60Hz, 1 Minute	4000	V~
Weight		5	g

Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- 4000V~ Electrical Isolation
- High Blocking Voltage
- High Peak Current Capability
- Low Saturation Voltage

Advantages

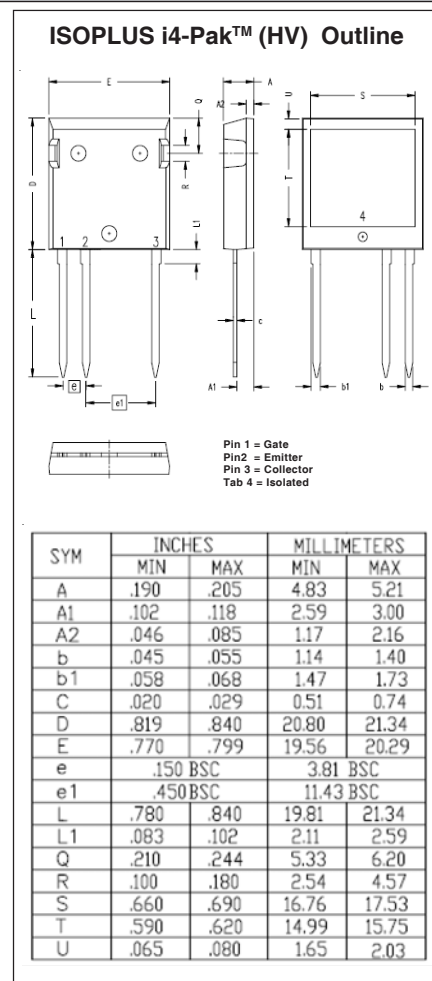
- Low Gate Drive Requirement
- High Power Density

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- Uninterruptible Power Supplies (UPS)
- Laser Generators
- Capacitor Discharge Circuits
- AC Switches

Symbol	Test Conditions ($T_J = 25^\circ C$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	3000		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	2.5		5.0 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$, $V_{GE} = 0V$ Note 2, $T_J = 125^\circ C$			35 μA 1.5 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 20A$, $V_{GE} = 15V$, Note 1 $T_J = 125^\circ C$		2.7	3.2 V
			3.2	V

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 20\text{A}, V_{CE} = 10\text{V}$, Note 1	11	18	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		2230	pF
C_{oes}			92	pF
C_{res}			33	pF
Q_g	$I_C = 20\text{A}, V_{GE} = 15\text{V}, V_{CE} = 1000\text{V}$		105	nC
Q_{ge}			13	nC
Q_{gc}			45	nC
$t_{d(on)}$	Resistive Switching Times, $T_J = 25^\circ\text{C}$ $I_C = 20\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 1250\text{V}, R_G = 10\Omega$		64	ns
t_r			210	ns
$t_{d(off)}$			300	ns
t_f			504	ns
$t_{d(on)}$	Resistive Switching Times, $T_J = 125^\circ\text{C}$ $I_C = 20\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 1250\text{V}, R_G = 10\Omega$		68	ns
t_r			540	ns
$t_{d(off)}$			300	ns
t_f			395	ns
R_{thJC}			0.83	$^\circ\text{C/W}$
R_{thCS}		0.15		$^\circ\text{C/W}$



Reverse Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
V_F	$I_F = 20\text{A}, V_{GE} = 0\text{V}$			2.1 V
t_{rr}	$I_F = 10\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}$		1.35	μs
I_{RM}		$V_R = 100\text{V}, V_{GE} = 0\text{V}$		30

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Device must be heatsunk for high temperature leakage current measurements to avoid thermal runaway.

IXYS Reserves the Right to Change Limits, Test Conditions and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

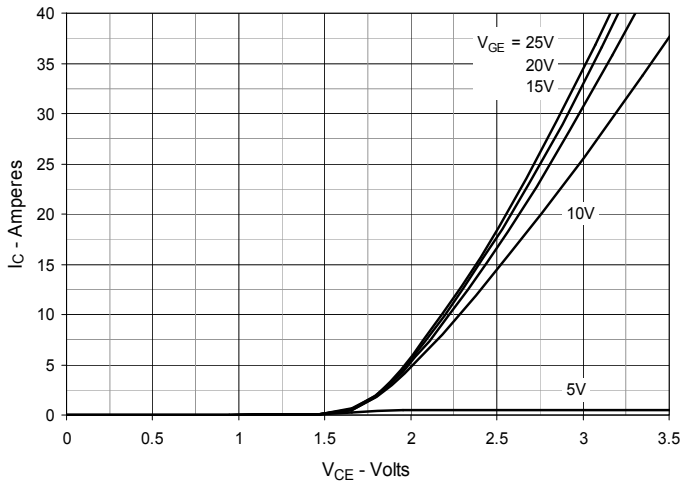


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

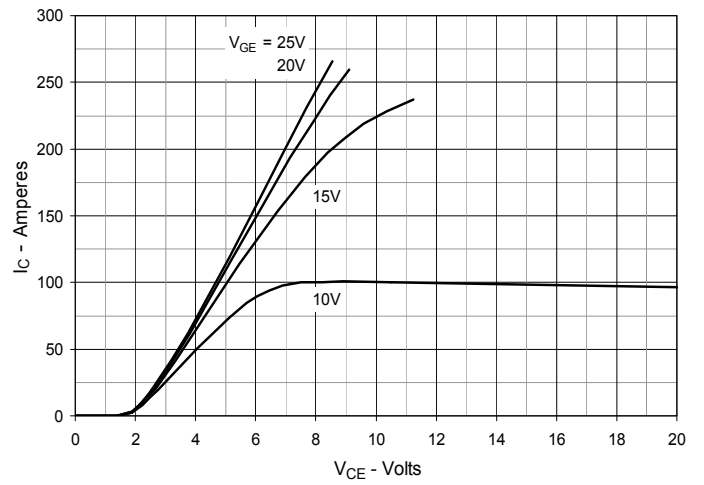


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

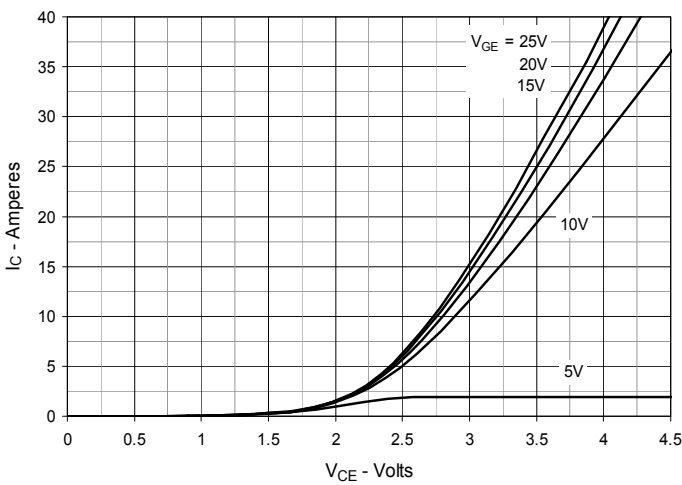


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

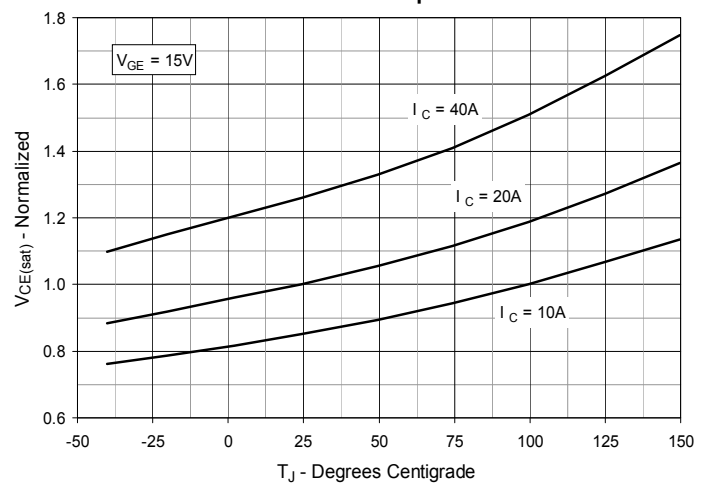


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

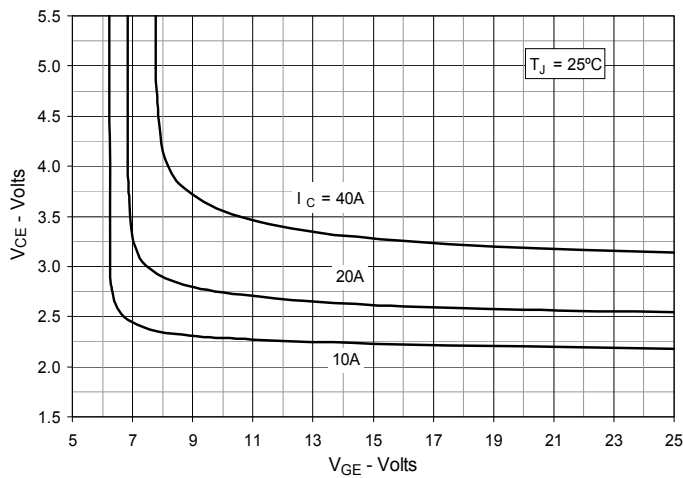


Fig. 6. Input Admittance

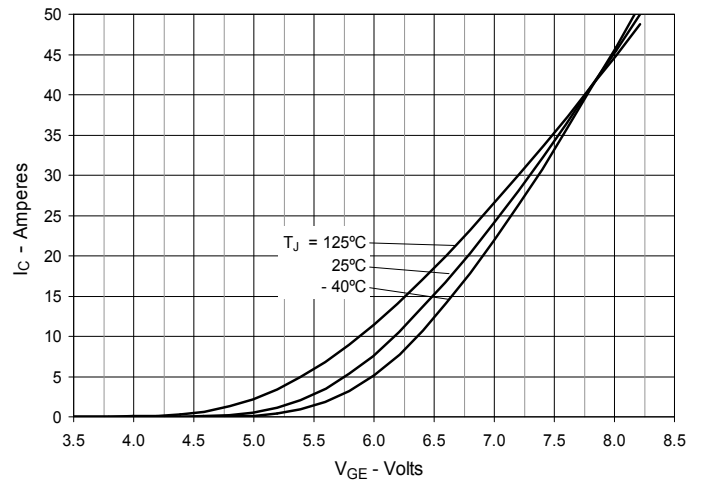


Fig. 7. Transconductance

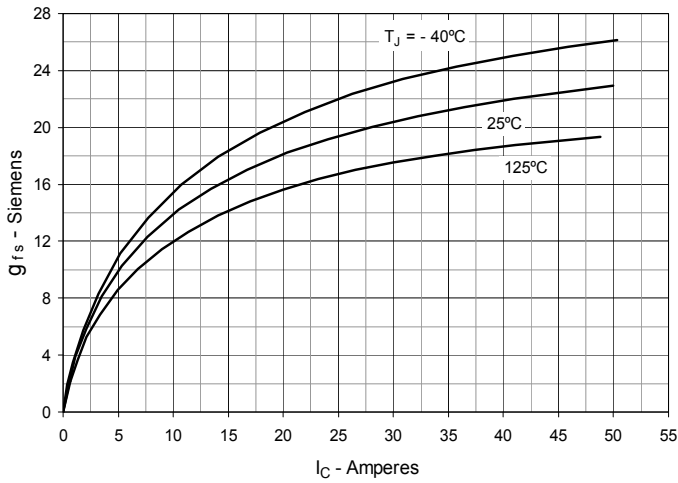


Fig. 8. Forward Voltage Drop of Intrinsic Diode

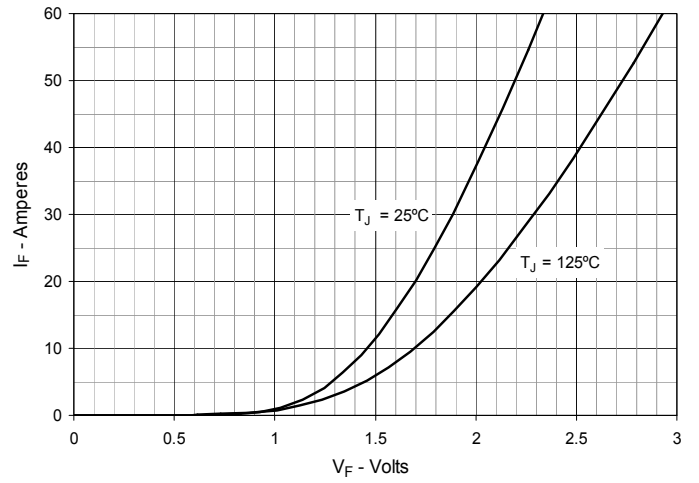


Fig. 9. Gate Charge

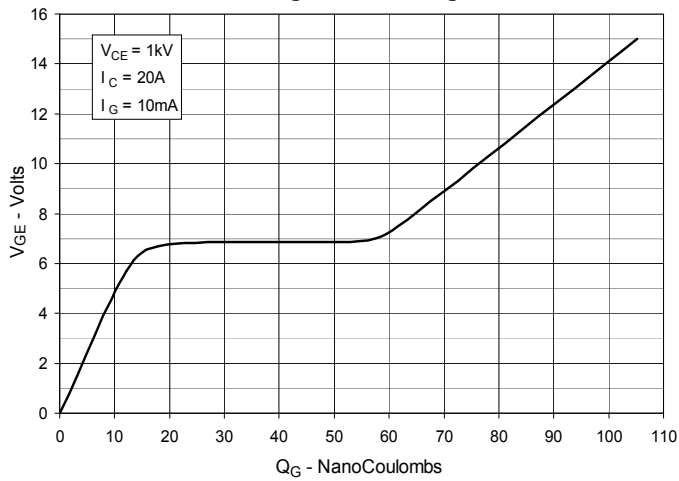


Fig. 10. Capacitance

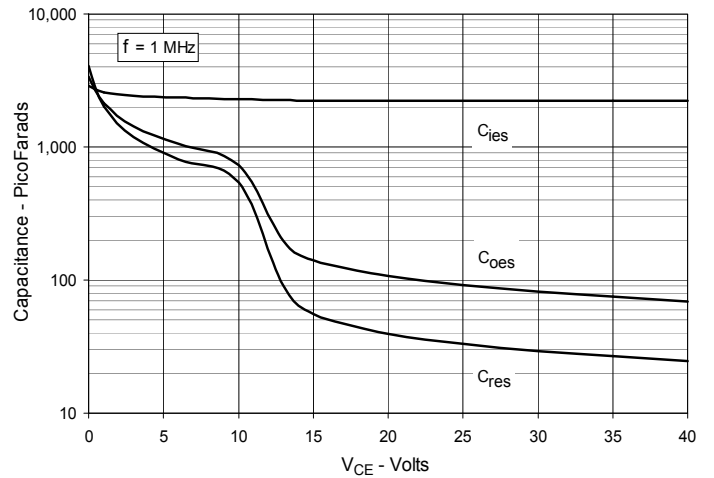


Fig. 11. Reverse-Bias Safe Operating Area

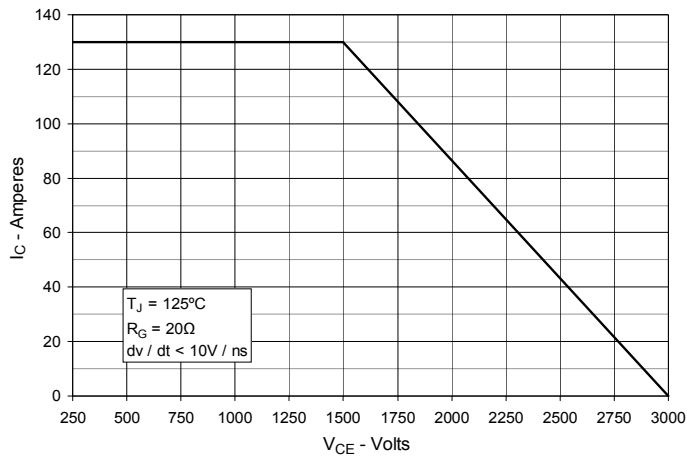


Fig. 12. Maximum Transient Thermal Impedance

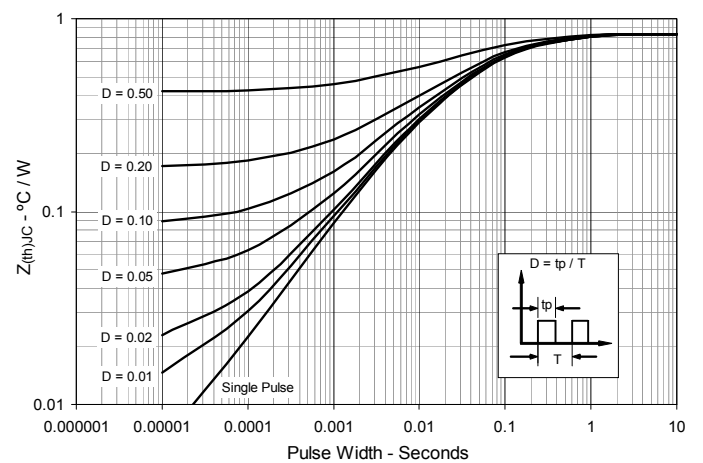
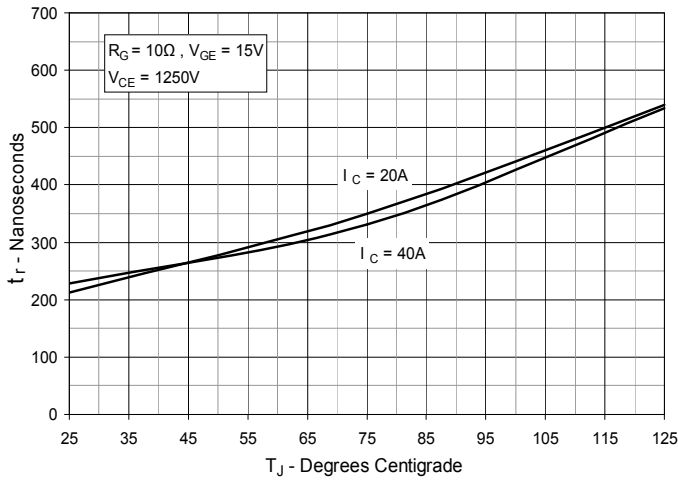
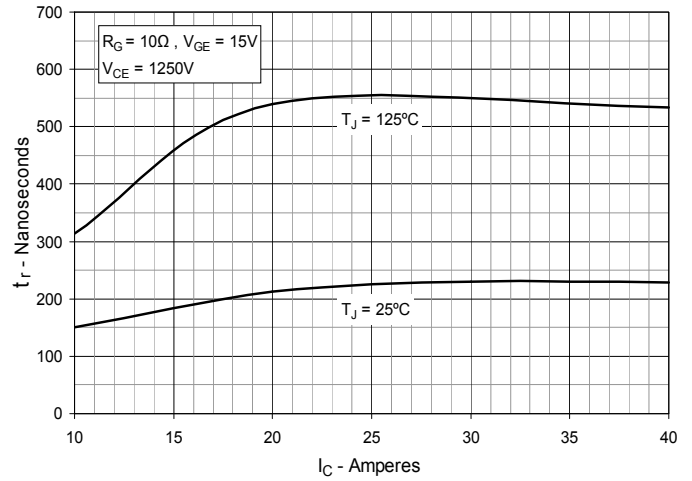
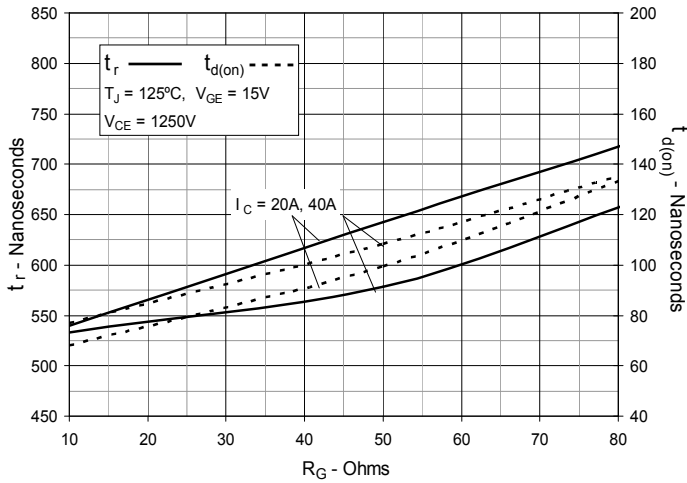
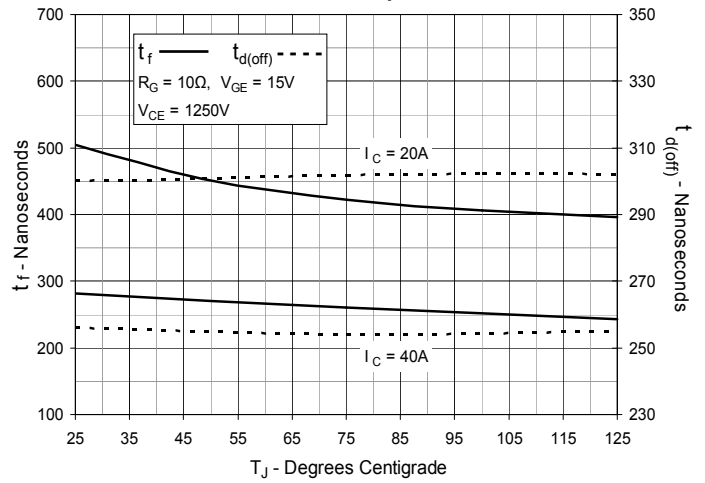
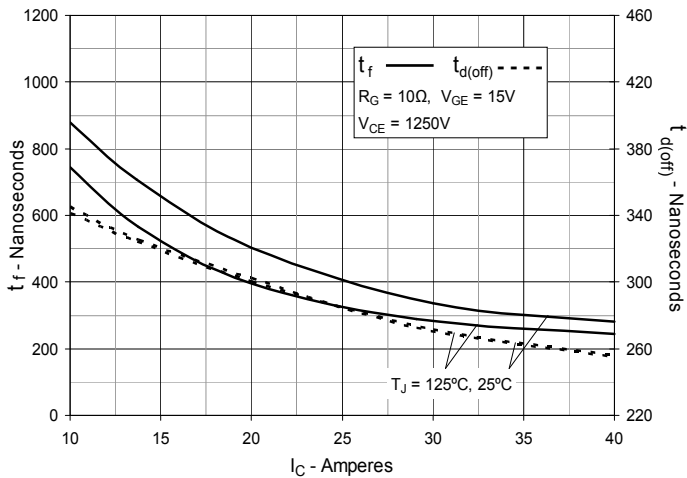


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

Fig. 14. Resistive Turn-on Rise Time vs. Collector Current

Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

Fig. 17. Resistive Turn-off Switching Times vs. Collector Current

Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance
